### **Sonic Fast Recovery Diode**

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

#### Part number

DH20-18A



Backside: cathode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:

Terms Conditions of usage:

- Power dissipation within the diode
- Turn-on loss in the commutating switch

#### **Applications:**

- Antiparallel diode for high frequency
- switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

#### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

- The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The

  - information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend
  - to perform joint risk and quality assessments;
    the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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### **DH20-18A**

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$V_{\text{RRM}}$	=	1800 V
I <sub>FAV</sub>	=	20 A
t <sub>rr</sub>	=	300 ns

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Fast Dio	de			1	Rating	5	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			1800	V
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			1800	V
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> =1800 V	$T_{VJ} = 25^{\circ}C$			50	μA
		V <sub>R</sub> =1800 V	$T_{vJ} = 125^{\circ}C$			0.2	mA
VF	forward voltage drop	I <sub>F</sub> = 20 A	$T_{VJ} = 25^{\circ}C$			2.24	V
		I <sub>F</sub> = 40 A				2.83	V
		I <sub>F</sub> = 20 A	T <sub>vj</sub> = 125°C			2.35	V
		$I_{F} = 40 \text{ A}$				3.25	V
	average forward current	T <sub>c</sub> = 95°C	T <sub>vJ</sub> = 150°C			20	Α
		rectangular d = 0.5					
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			1.44	V
r <sub>F</sub>	slope resistance } for power lo	oss calculation only				43	mΩ
$R_{thJC}$	thermal resistance junction to cas	e				0.9	K/W
R thCH	thermal resistance case to heatsir	nk			0.25		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			140	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0 V$	$T_{VJ} = 45^{\circ}C$			150	А
C	junction capacitance	$V_{R}$ = 900 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		7		pF
IRM	max. reverse recovery current	<b>N</b>	$T_{VJ} = 25 ^{\circ}C$		22		Α
		$I_{\rm F} = 20  \text{A};  V_{\rm R} = 900  \text{V}$	T <sub>vJ</sub> = 125 °C		25		Α
t <sub>rr</sub>	reverse recovery time	$\begin{cases} I_{F} = 20 \text{ A}; V_{R} = 900 \text{ V} \\ -di_{F} / dt = 400 \text{ A} / \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		300		ns
		)	T <sub>vJ</sub> = 125 °C		550		ns

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Package TO-247				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal			70	А
T <sub>vj</sub>	virtual junction temperature		-5	5	150	°C
T <sub>op</sub>	operation temperature		-55	5	125	°C
T <sub>stg</sub>	storage temperature		-5	5	150	°C
Weight				6		g
M <sub>D</sub>	mounting torque		0.8	3	1.2	Nm
F <sub>c</sub>	mounting force with clip		20	)	120	Ν

**Product Marking** 



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DH20-18A	DH20-18A	Tube	30	499730

Equiva	alent Circuits for	Simulation	* on die level	T <sub>vj</sub> = 150 °C
	) Ro	Fast Diode		
V <sub>0 max</sub>	threshold voltage	1.44		V
$R_{0 max}$	slope resistance *	40		mΩ

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~ F	D2			
ØF		Sym.	Inch	nes
-/			min.	ma
$\checkmark$ 1		Α	0.185	0.2
77 I		A1	0.087	0.1
		A2	0.059	0.0
	D1	D	0.819	0.8
		E	0.610	0.6
		E2	0.170	0.2
4		е	0.430	BS
	<u> </u>	L	0.780	0.8
		L1	-	0.1
	1	ØР	0.140	0.1
		Q	0.212	0.2
		S	0.242	BS
		b	0.039	0.0
		b2	0.065	0.0
		b4	0.102	0.1
			0.045	~ ~

-E1

Sym.	Inch	ies	Millimeter		
-	min.	max.	min.	max.	
А	0.185	0.209	4.70	5.30	
A1	0.087	0.102	2.21	2.59	
A2	0.059	0.098	1.50	2.49	
D	0.819	0.845	20.79	21.45	
Е	0.610	0.640	15.48	16.24	
E2	0.170	0.216	4.31	5.48	
е	0.430	BSC	10.92	BSC	
L	0.780	0.800	19.80	20.30	
L1	-	0.177	-	4.49	
ØР	0.140	0.144	3.55	3.65	
Q	0.212	0.244	5.38	6.19	
S	0.242	BSC	6.14	BSC	
b	0.039	0.055	0.99	1.40	
b2	0.065	0.094	1.65	2.39	
b4	0.102	0.135	2.59	3.43	
с	0.015	0.035	0.38	0.89	
D1	0.515	-	13.07	-	
D2	0.020	0.053	0.51	1.35	
E1	0.530	-	13.45	-	
ØP1	-	0.29	-	7.39	



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Fig. 7 Typ. transient thermal impedance junction to case

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